

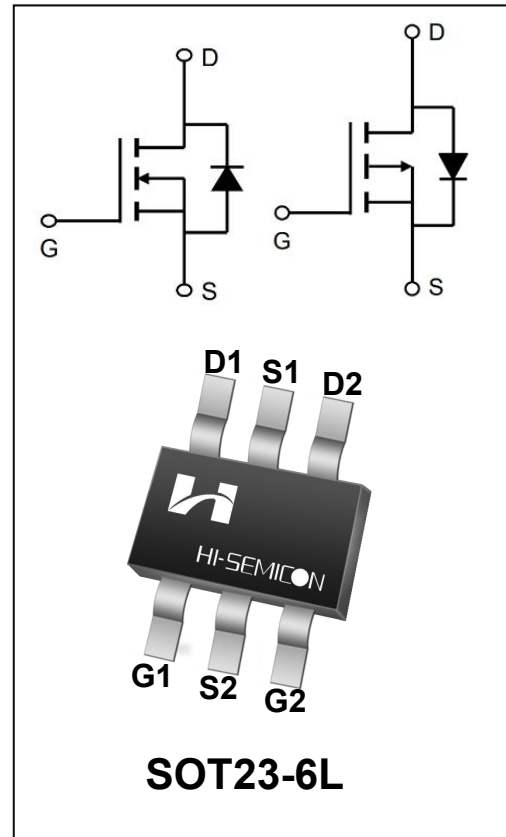
N and P-CHANNEL POWER MOSFET

GENERAL DESCRIPTION

The SS0405T4 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

FEATURES

- ◆ N-CHANNEL
 - $V_{DS}=40V, I_D=5A$
 - $R_{DS(ON)}=28m\Omega(TYP@V_{GS}=10V)$
 - $R_{DS(ON)}=34m\Omega(TYP@V_{GS}=4.5V)$
- ◆ P-CHANNEL
 - $V_{DS}=-40V, I_D=-7A$
 - $R_{DS(ON)}=46m\Omega(TYP@V_{GS}=-10V)$
 - $R_{DS(ON)}=65m\Omega(TYP@V_{GS}=-4.5V)$
- ◆ High density cell design for ultra low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC Current capability



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SS0405T4	SOT23-6L	0405T4	Pb Free	Reel

ABSOLUTE MAXIMUM RATINGS (T_J=25°C unless otherwise noted)

Characteristics		Symbol	N-CHANNEL	P-CHANNEL	UNIT
Drain-Source Voltage		V _{DS}	40	-40	V
Gate-Source Voltage		V _{GS}	±20	±20	V
Drain Current	TC=25°C	I _D	5	-7.0	A
	TC=70°C		3.8	-5.1	A
Pulsed Drain Current(note1)		I _{DM}	20	-28	A
Power Dissipation	TC=25°C	P _D	1.67		W
Thermal Characteristics					
Thermal Resistance, Junction-to-Ambient		R _{θJA}	75		°C/W
Junction and Storage Temperature Range		T _J ,T _{stg}	-55 to +150		°C
Maximum lead temperature for soldering purposes,1/8" from case for 5 seconds		TL	300		°C

N-CHANNEL ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain -Source Breakdown Voltage	B _{VDS}	V _{GS} =0V, I _D =250μA	40	44	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	--	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =20V, V _{DS} =0V	-	--	100	nA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =-20V, V _{DS} =0V	-	--	-100	
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	0.9	1.35	1.8	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3A	-	28	33	mΩ
		V _{GS} =4.5V, I _D =2A	-	34	40	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V	-	511.9	-	pF
Output Capacitance	C _{oss}	V _{GS} =0V	-	53.5	-	
Reverse Transfer Capacitance	C _{rss}	f=1.0MHZ	-	37.8	-	
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, V _{GS} =10V R _G =3.3Ω, I _D =3A (Note 2.3)	-	7.9	-	ns
Turn-on Rise Time	t _r		-	2.2	-	
Turn-off Delay Time	t _{d(off)}		-	28.7	-	
Turn-off Fall Time	t _f		-	2.1	-	
Total Gate Charge	Q _g	V _{DS} =15V, I _D =3A V _{GS} =4.5V (Note 2.3)	-	5.1	-	nC
Gate-Source Charge	Q _{gs}		-	1.55	-	
Gate-Drain Charge	Q _{gd}		-	1.86	-	

N-CHANNEL SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	-	-	5	A
Pulsed Source Current	I_{SM}		-	-	20	
Diode Forward Voltage	V_{SD}	$I_S=5A, V_{GS}=0V$	-	--	1.4	V

P-CHANNEL ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain -Source Breakdown Voltage	B_{VDSS}	$V_{GS}=0V, I_D=-250\mu A$	-40	-44	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=-20V, V_{DS}=0V$	-	-	-100	
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.1	-1.7	-2.2	V
Static Drain- Source On State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-5A$	-	46	55	$m\Omega$
		$V_{GS}=-4.5V, I_D=-3A$	-	65	80	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-25V$ $V_{GS}=0V$ $f=1.0MHz$	-	662.7	-	pF
Output Capacitance	C_{oss}		-	53.5	-	
Reverse Transfer Capacitance	C_{rss}		-	419.4	-	
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, V_{GS}=-10V$ $R_G=3\Omega, I_D=-5A$ (Note 2.3)	-	4.4	-	ns
Turn-on Rise Time	t_r		-	23.3	-	
Turn-off Delay Time	$t_{d(off)}$		-	27.1	-	
Turn-off Fall Time	t_f		-	21.2	-	
Total Gate Charge	Q_g	$V_{DS}=-20V, I_D=-5A$ $V_{GS}=-10V$ (Note 2.3)	-	6.5	-	nC
Gate-Source Charge	Q_{gs}		-	2.2	-	
Gate-Drain Charge	Q_{gd}		-	2.6	-	

P-CHANNEL SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	-	-	-7	A
Pulsed Source Current	I_{SM}		-	-	-28	
Diode Forward Voltage	V_{SD}	$I_S=-7A, V_{GS}=0V$	-	--	-1.4	V

- 1.Pulse width limited by maximum junction temperature
- 2.Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
- 3.Essentially independent of operating temperature

N-CHANNEL Typical Performance Characteristics

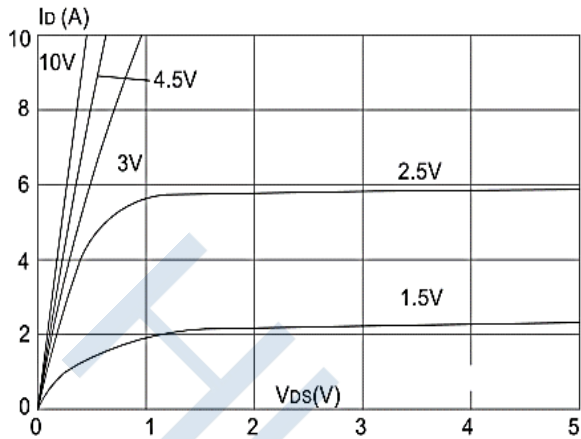


Figure 1: Output Characteristics

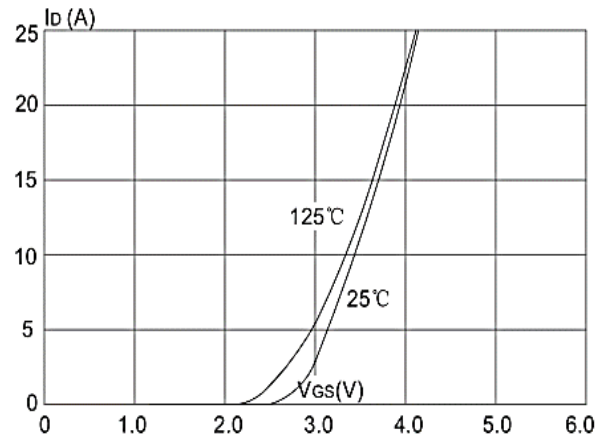


Figure 2: Typical Transfer Characteristics

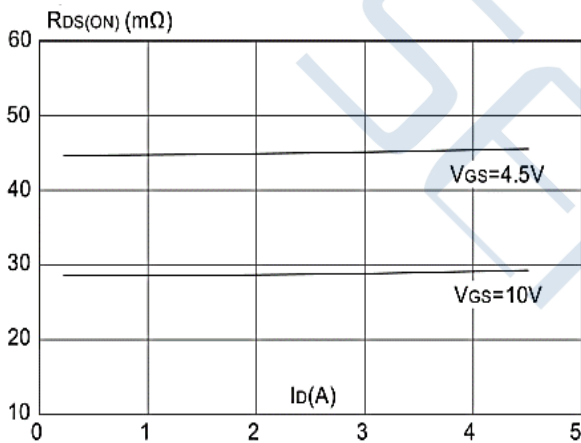


Figure 3: On-resistance vs. Drain Current

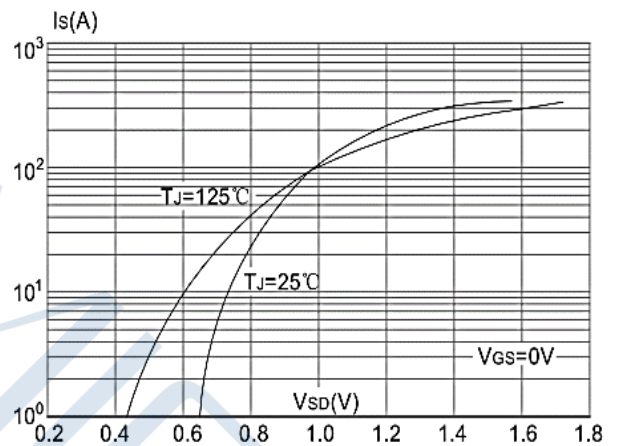


Figure 4: Body Diode Characteristics

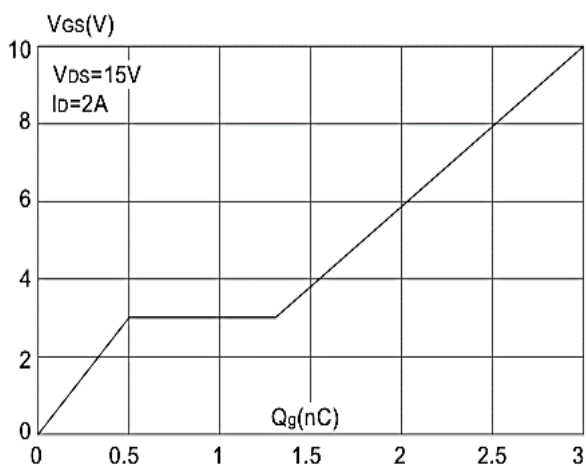


Figure 5: Gate Charge Characteristics

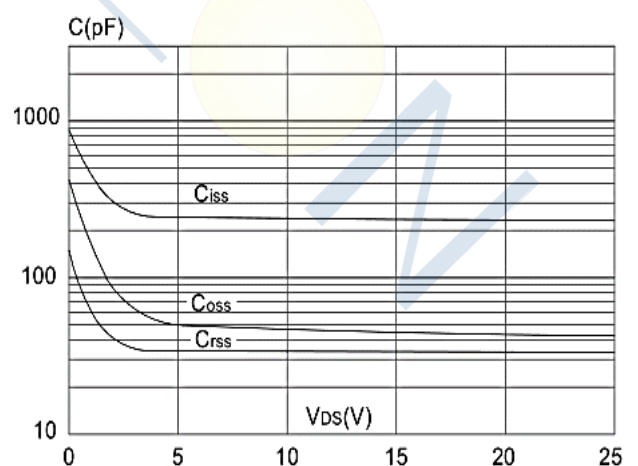


Figure 6: Capacitance Characteristics

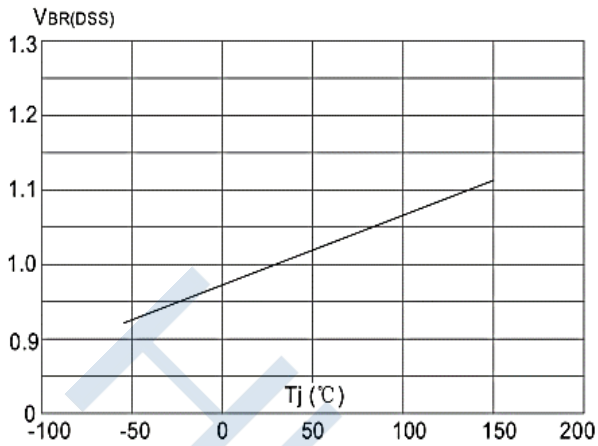


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

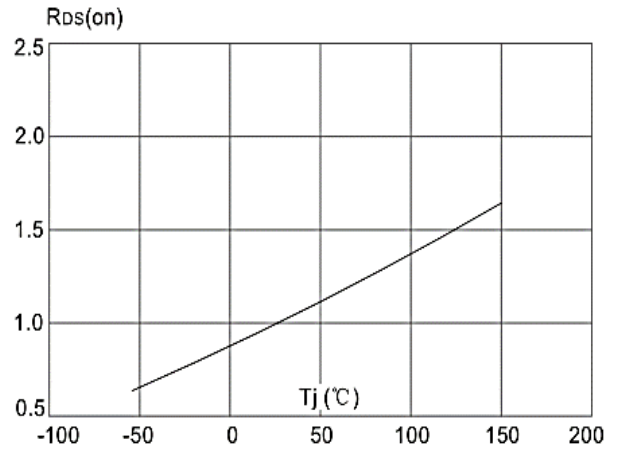


Figure 8: Normalized on Resistance vs. Junction Temperature

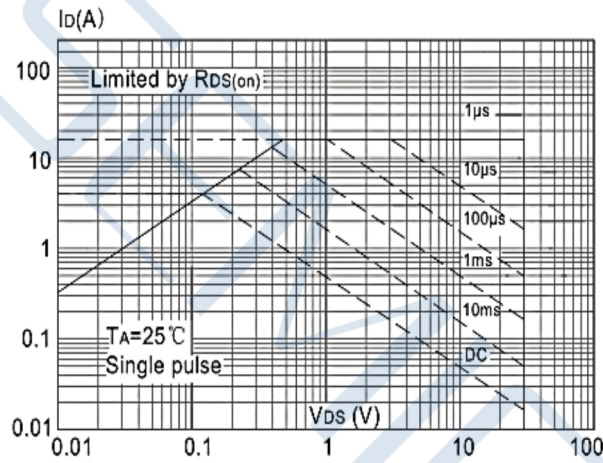


Figure 9: Maximum Safe Operating Area vs. Case Temperature

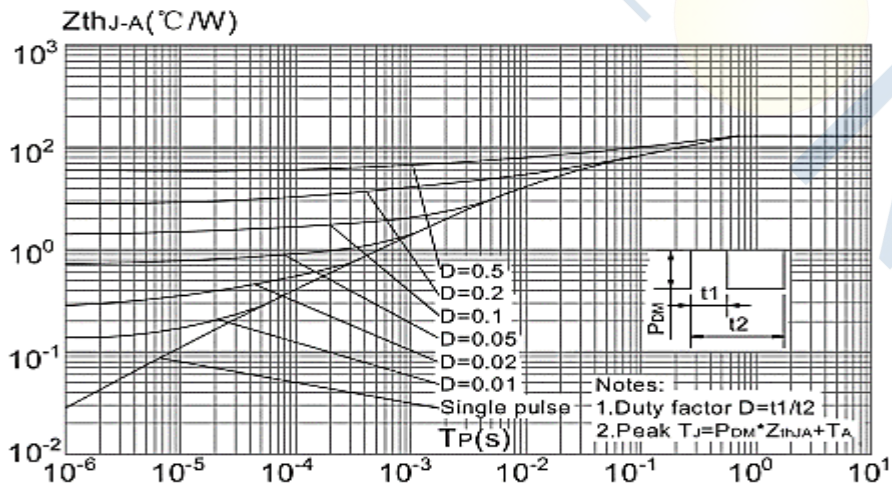


Figure.10: Maximum Effective Transient Thermal Impedance, Junction-to-Case

P-CHANNEL Typical Performance Characteristics

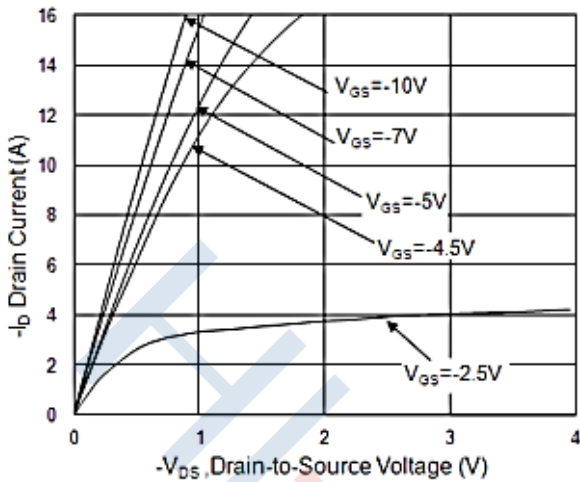


Fig.1 Typical Output Characteristics

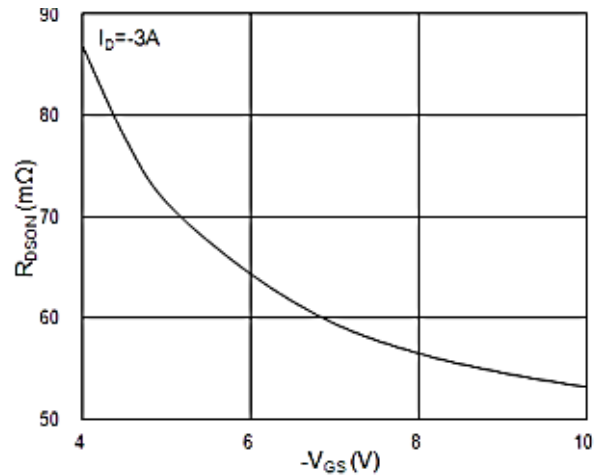


Fig.2 On-Resistance vs. G-S Voltage

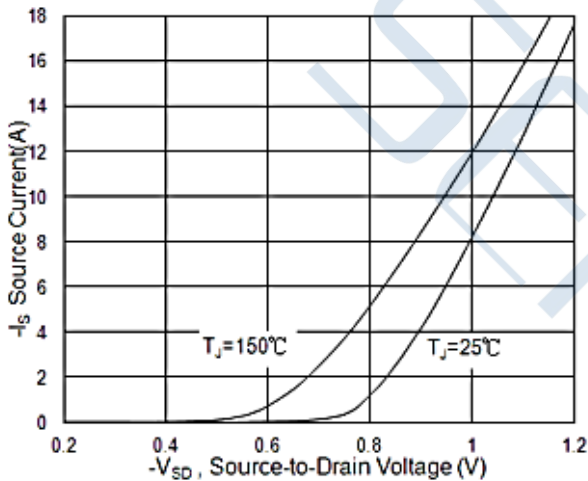


Fig.3 Forward Characteristics Of Reverse

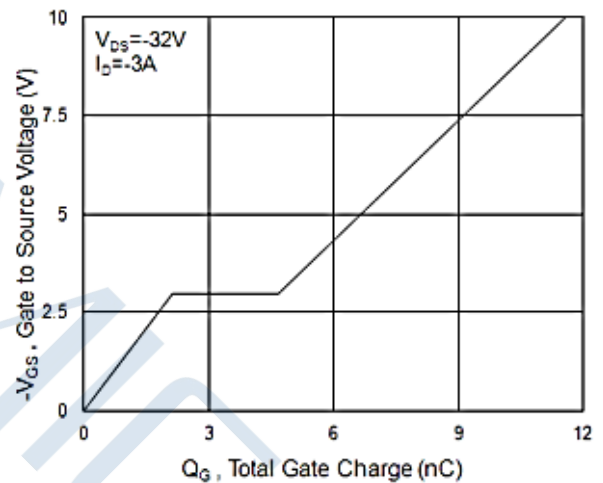


Fig.4 Gate-Charge Characteristics

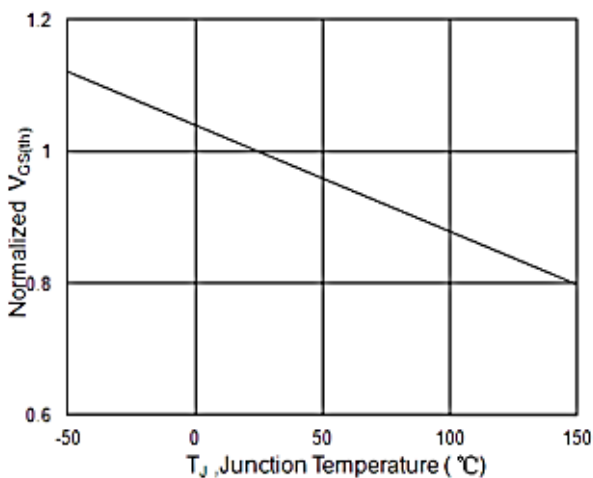


Fig.5 Normalized $V_{GS(th)}$ vs. $T_{J,DC}$.

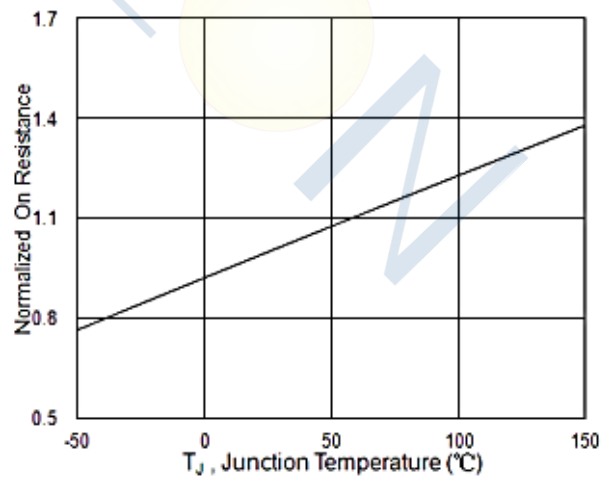


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

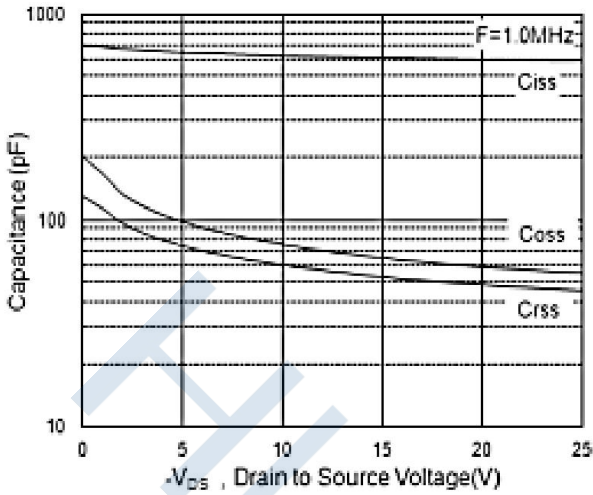


Fig.7 Capacitance

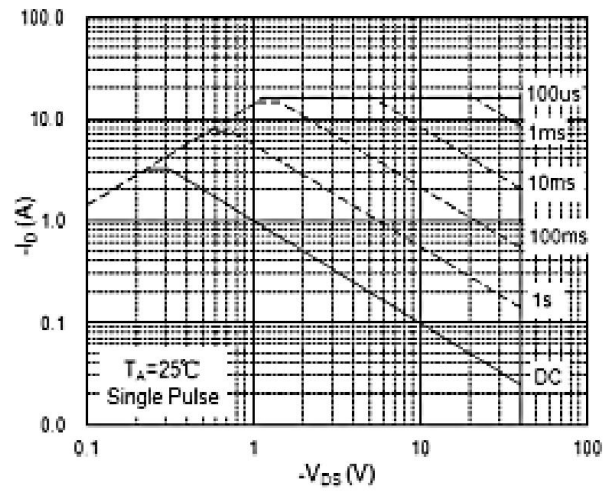


Fig.8 Safe Operating Area

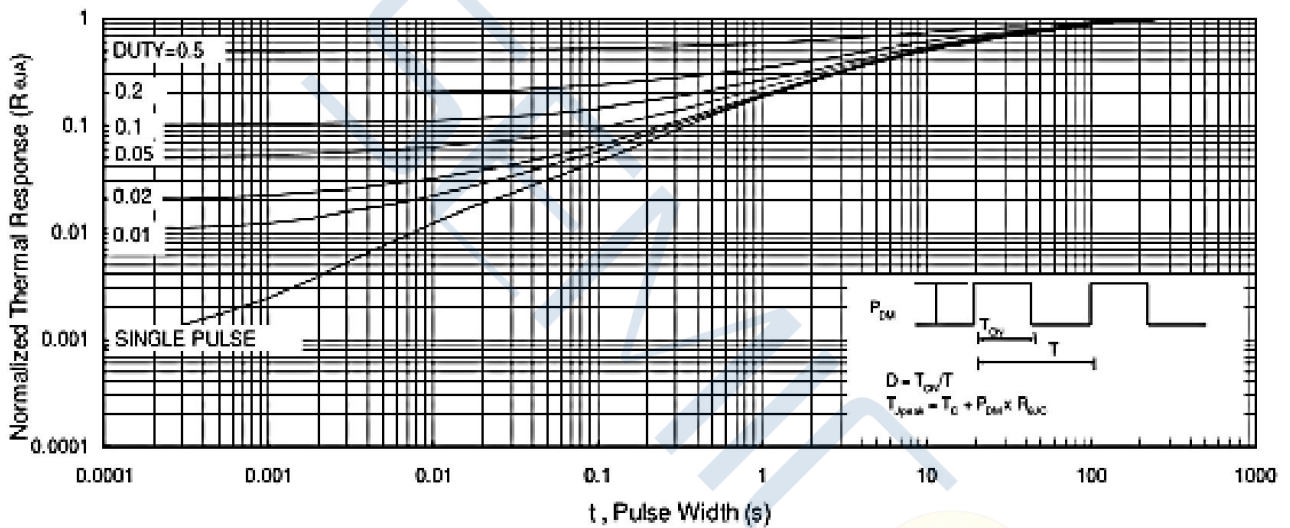
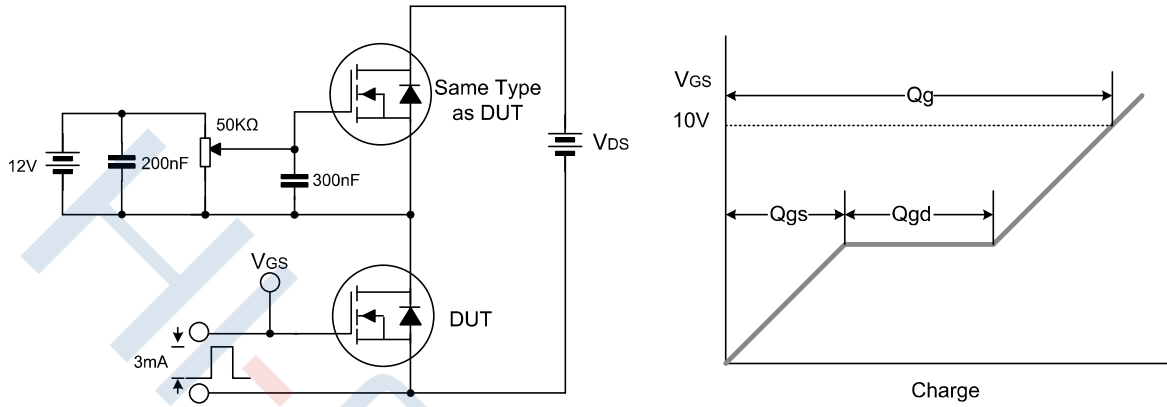


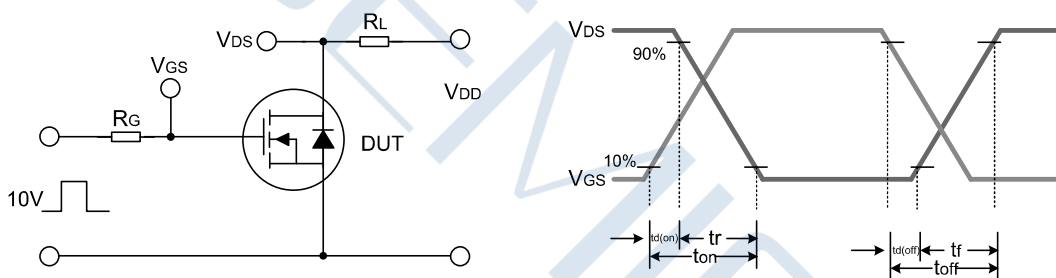
Fig.9 Normalized Maximum Transient Thermal Impedance

Test Circuit

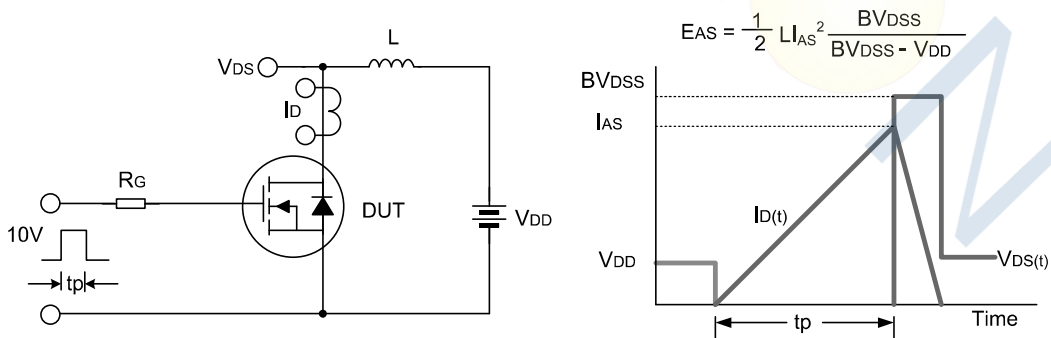
Gate Charge Test Circuit & Waveform



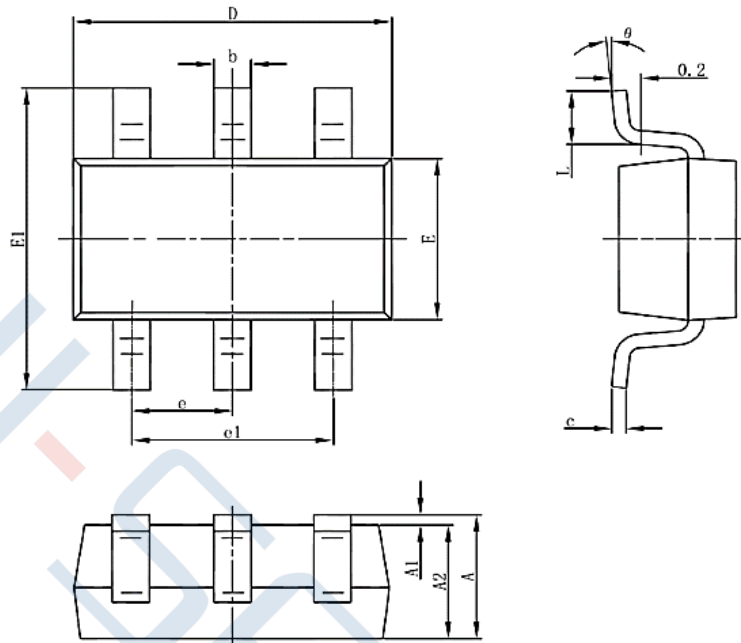
Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



Package Dimensions of SOT23-6L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950 (BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
theta	0	8	0	8

Disclaimer:

- ▶ Hi-semicon reserves the right to make changes to the information herein for the improvement of the design and performance without further notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- ▶ All semiconductor products malfunction or fail with some probability under special conditions. When using Hi-semicon products in system design or complete machine manufacturing, it is the responsibility of the buyer to comply with the safety standards strictly and take essential measures to avoid situations in which a malfunction or failure of such Hi-semicon products could cause loss of body injury or damage to property.
- ▶ Hi-semicon will supply the best possible product for customers!